Product data sheet

1. General description

2x30A, 300V dual ultrafast power diode in a SOT429 (3-lead TO-247) plastic package.

2. Features and benefits

- Low forward voltage drop
- Fast Switching
- Soft recovery characteristics
- High thermal cycling performance
- Low thermal resistance

3. Applications

- Telecom power supplies
- Welding machines
- Secondary rectification in SMPS

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V_{RRM}	repetitive peak reverse voltage			-	-	300	V
I _{F(AV)}	average forward current	δ = 0.5 ; T _{mb} ≤ 103 °C; square-wave pulse; per diode; <u>Fig. 1</u> ; <u>Fig. 2</u> ; <u>Fig. 3</u>		-	-	30	А
I _{O(AV)}	average output current	δ = 0.5 ; T _{mb} ≤ 103 °C; square-wave pulse; both diodes conducting		-	-	60	А
I _{FRM}	repetitive peak forward current	δ = 0.5 ; t _p = 25 µs; square-wave pulse; per diode		-	-	60	А
I _{FSM}	non-repetitive peak forward current	t_p = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; per diode; Fig. 4		-	-	300	А
		t_p = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; per diode; Fig. 4		-	-	330	А
Static charact	eristics		,				
V _F	forward voltage	I _F = 30 A; T _j = 25 °C; <u>Fig. 6</u>		-	1	1.25	V
		I _F = 30 A; T _j = 150 °C; <u>Fig. 6</u>		-	0.85	1	V





Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Dynamic ch	naracteristics					_
t _{rr}	reverse recovery time	$I_F = 1 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 50 \text{ A/}\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 7$	-	-	50	ns
		$I_F = 30 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A}/$ $\mu s; T_j = 25 ^{\circ}\text{C}; Fig. 7$	-	33	-	ns
		$I_F = 30 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A}/$ $\mu s; T_j = 125 \text{ °C}; Fig. 7$	-	62	-	ns

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	A1	anode 1		A1 A2
2	K	cathode		<u> </u>
3	A2	anode 2		sym125
mb	К	mounting base; cathode		
			TO-247 (SOT429)	

6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BYV430W-300P	TO-247	plastic single-ended through-hole package; heatsink mounted; 1 mounting hole; 3 lead TO-247	SOT429

7. Marking

Table 4. Marking codes

Type number	Marking code
BYV430W-300P	BYV430W-300P

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{RRM}	repetitive peak reverse voltage		-	300	V
V_{RWM}	crest working reverse voltage		-	300	V
V_R	reverse voltage	DC	-	300	V
I _{F(AV)}	average forward current	δ = 0.5 ; T _{mb} ≤ 103 °C; square-wave pulse; per diode; <u>Fig. 1</u> ; <u>Fig. 2</u> ; <u>Fig. 3</u>	-	30	A
I _{O(AV)}	average output current	δ = 0.5 ; T _{mb} ≤ 103 °C; square-wave pulse; both diodes conducting	-	60	A
I _{FRM}	repetitive peak forward current	δ = 0.5 ; t _p = 25 µs; square-wave pulse; per diode	-	60	A
I _{FSM}	non-repetitive peak forward current	t_p = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; per diode; Fig. 4	-	300	A
		t_p = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; per diode; Fig. 4	-	330	A
T _{stg}	storage temperature		-55	175	°C
T _j	junction temperature		-	175	°C

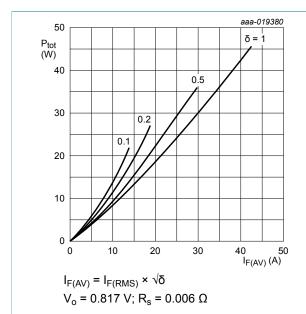


Fig. 1. Forward power dissipation as a function of average forward current; square waveform; per diode; maximum values

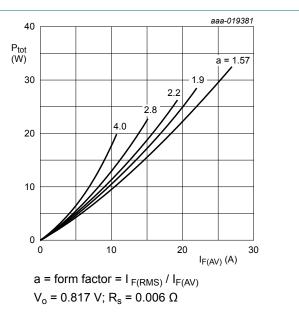


Fig. 2. Forward power dissipation as a function of average forward current; sinusoidal waveform; per diode; maximum values

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Dual ultrafast power diode

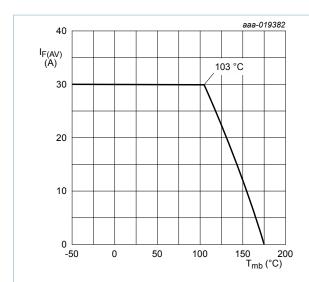


Fig. 3. Average forward current as a function of mounting base temperature; per diode; maximum values

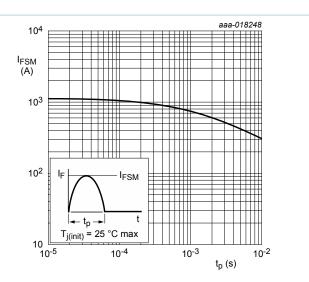


Fig. 4. Non-repetitive peak forward current as a function of pulse width; sinusoidal waveform; per diode; maximum values

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)} thermal resistance from junction to mounting base	from junction to	with heatsink compound; per diode; Fig. 5	-	8.0	2	K/W
	with heatsink compound; both diodes conducting	-	-	1.2	K/W	
R _{th(j-a)}	thermal resistance from junction to ambient free air	in free air	_	45	-	K/W

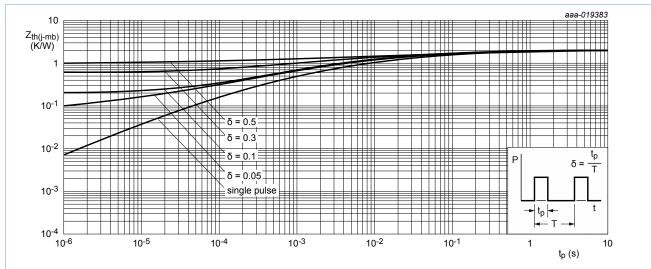


Fig. 5. Transient thermal impedance from junction to mounting base as a function of pulse duration; per diode; maximum values

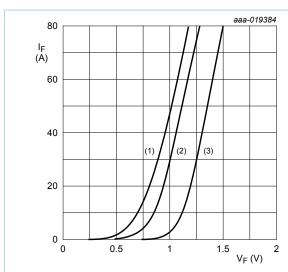
10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static char	acteristics					
V _F	forward voltage	I _F = 30 A; T _j = 25 °C; <u>Fig. 6</u>	-	1	1.25	V
		I _F = 30 A; T _j = 150 °C; <u>Fig. 6</u>	-	0.85	1	V
I _R	reverse current	V _R = 300 V; T _j = 25 °C	-	0.4	10	μA
		V _R = 300 V; T _j = 150 °C	-	-	500	μΑ
Dynamic c	haracteristics					
Q _r recovered c	recovered charge	$I_F = 30 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A}/$ $\mu s; T_j = 25 ^{\circ}\text{C}; Fig. 7$	-	89	-	nC
		$I_F = 30 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A}/$ $\mu s; T_j = 125 \text{ °C}; Fig. 7$	-	337	-	nC
t _{rr}	reverse recovery time	$I_F = 1 \text{ A}$; $V_R = 30 \text{ V}$; $dI_F/dt = 50 \text{ A}/\mu\text{s}$; $T_j = 25 \text{ °C}$; Fig. 7	-	-	50	ns
		$I_F = 30 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A}/$ $\mu s; T_j = 25 \text{ °C}; Fig. 7$	-	33	-	ns
		$I_F = 30 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A}/$ $\mu s; T_j = 125 \text{ °C}; Fig. 7$	-	62	-	ns
I _{RM}	peak reverse recovery current	$I_F = 30 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A}/$ $\mu s; T_j = 25 \text{ °C}; Fig. 7$	-	5.3	-	Α
		$I_F = 30 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A}/$ $\mu s; T_j = 125 \text{ °C}; Fig. 7$	-	10.5	-	Α

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Dual ultrafast power diode



 V_o = 0.817 V; R_s = 0.006 Ω

(1) T_j = 150 °C; typical values

(2) T_i = 150 °C; maximum values

(3) T_i = 25 °C; maximum values

Fig. 6. Forward current as a function of forward voltage, per diode

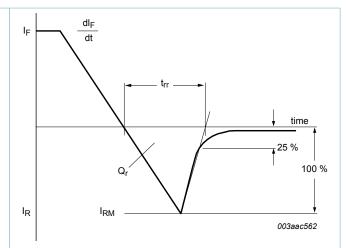
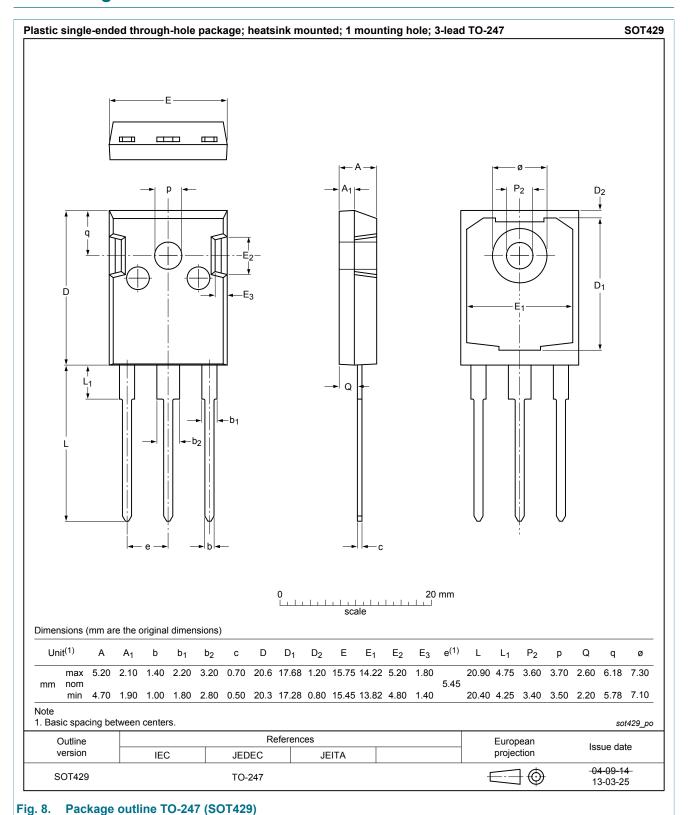


Fig. 7. Reverse recovery definitions; ramp recovery

Product data sheet

11. Package outline



12. Legal information

12.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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